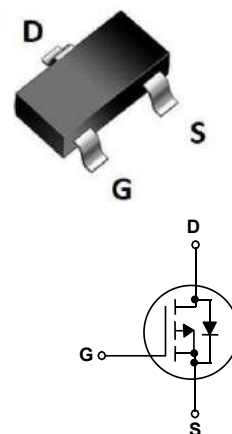


Features

- P-Channel
- Good stability and uniformity
- 100% avalanche tested
- Excellent package for good heat dissipation

V_{DS}	-20	V
$R_{DS(on),TYP@ V_{GS}=-4.5 V}$	29	m Ω
$R_{DS(on),TYP@ V_{GS}=-2.5 V}$	40	m Ω
I_D	-5	A

SOT-23


Part ID	Package Type	Marking	Packing
ZT2305	SOT-23	2305	3000pcs/Reel

Absolute Maximum Ratings $T_A = 25^\circ\text{C}$, unless otherwise specified

Symbol	Parameter	Rating	Unit	
Common Ratings ($T_c=25^\circ\text{C}$ Unless Otherwise Noted)				
V_{GS}	Gate-Source Voltage	± 12	V	
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	-20	V	
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$	
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$	
I_{DM}	Drain Current-Continuous@ Current-Pulsed (Note 1)	$T_c = 25^\circ\text{C}$ -20	A	
Mounted on Large Heat Sink				
I_D	Drain Current-Continuous	$T_c = 25^\circ\text{C}$	-5	A
		$T_c = 100^\circ\text{C}$	-3.1	A
P_D	Maximum Power Dissipation - Derate above 25°C	$T_c = 25^\circ\text{C}$	1.5	W
		$T_c = 25^\circ\text{C}$	0.53	W/ $^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	83	$^\circ\text{C/W}$	

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T_J=25°C (unless otherwise stated)						
V(BR)DSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-20	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-20V, V _{GS} =0V	--	--	-1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±12V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-0.4	-0.7	-0.9	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-4.5V, I _D =-4.1A	--	29	42	mΩ
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-2.5V, I _D =-3A	--	40	58	mΩ
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated) (Note 3,4)						
C _{iss}	Input Capacitance	V _{DS} =-10V, V _{GS} =0V, f=1MHz	--	820	--	pF
C _{oss}	Output Capacitance		--	102	--	pF
C _{rss}	Reverse Transfer Capacitance		--	80	--	pF
Q _g	Total Gate Charge	V _{DS} =-10V, I _D =-4.1A, V _{GS} =-4.5V	--	7	--	nC
Q _{gs}	Gate-Source Charge		--	1	--	nC
Q _{gd}	Gate-Drain Charge		--	1.4	--	nC
Switching Characteristics (Note 3,4)						
T _{d(on)}	Turn-on Delay Time	V _{DD} =-10V, I _D =-4.1A, R _L =1Ω, R _G =1Ω, V _{GS} =-4.5V	--	14	--	ns
T _r	Turn-on Rise Time		--	60	--	ns
T _{d(off)}	Turn-Off Delay Time		--	20	--	ns
T _f	Turn-Off Fall Time		--	10	--	ns
Source- Drain Diode Characteristics @ T_J = 25°C (unless otherwise stated)						
I _{SD}	Source-Drain Current (Body Diode) (Note 2)		--	--	-5	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	-16	A
V _{SD}	Forward on voltage	I _S =-4.1A, V _{GS} =0V	--	--	-1.2	V
T _{rr}	Reverse Recovery Time	T _J =25°C, I _S =4.1A di/dt=100A/μs	--	16	--	ns
Q _{rr}	Reverse Recovery Charge		--	7	--	nC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. I_{SD} ≤ -4A, di/dt = 100A/μs, V_{DD} ≤ BV_{DSS}, Staring T_J =25°C
3. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%
4. Essentially independent of operating temperature

Typical Performance Characteristics

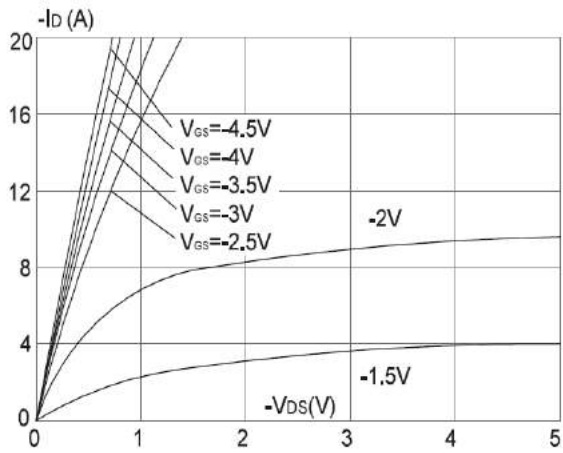


Figure1: Output Characteristics

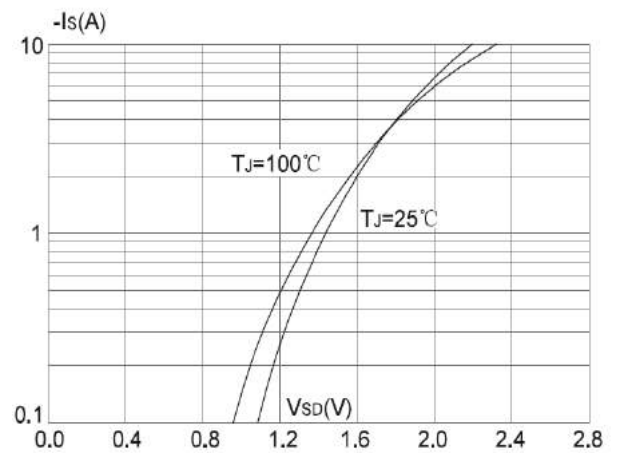


Figure 4: Body Diode Characteristics

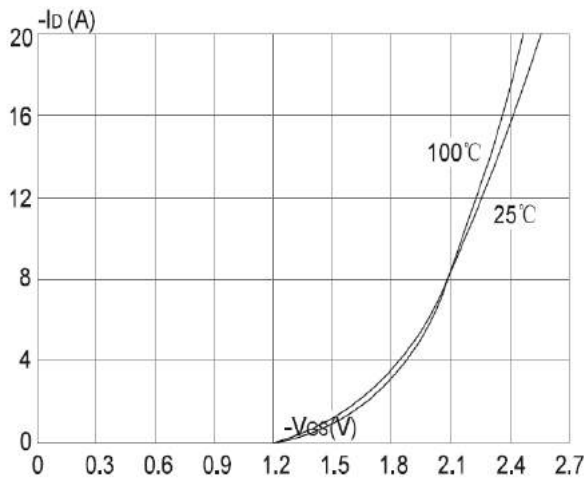


Figure 2: Typical Transfer Characteristics

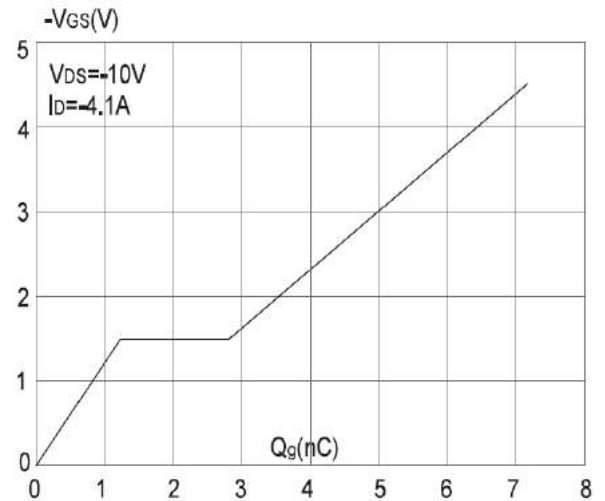


Figure 5: Gate Charge Characteristics

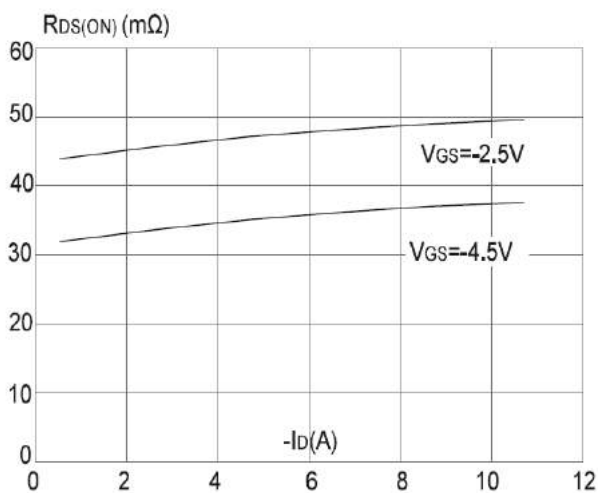


Figure 3: On-resistance vs. Drain Current

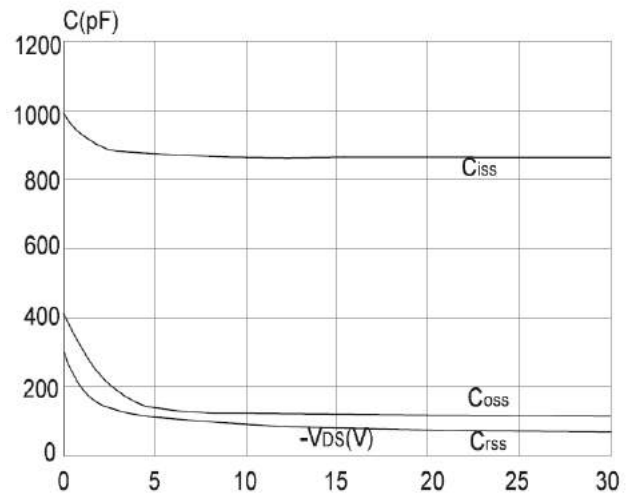


Figure 6: Capacitance Characteristics

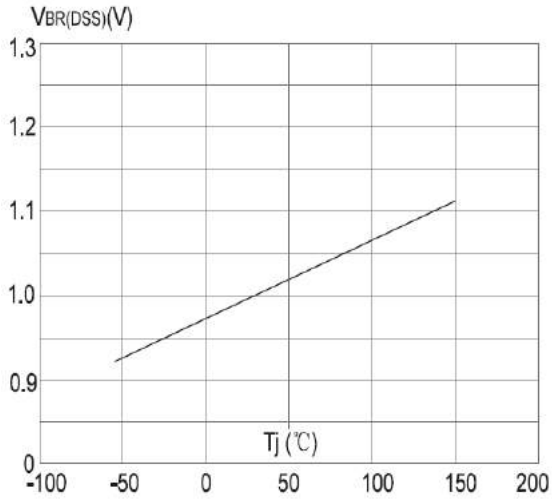


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

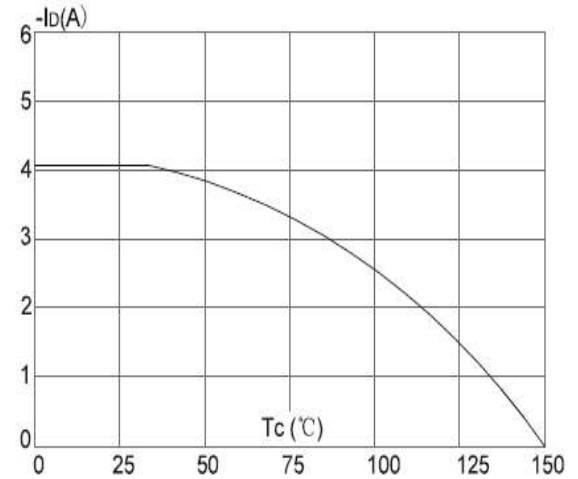


Figure 9: Maximum Drain Current vs. Case Temperature

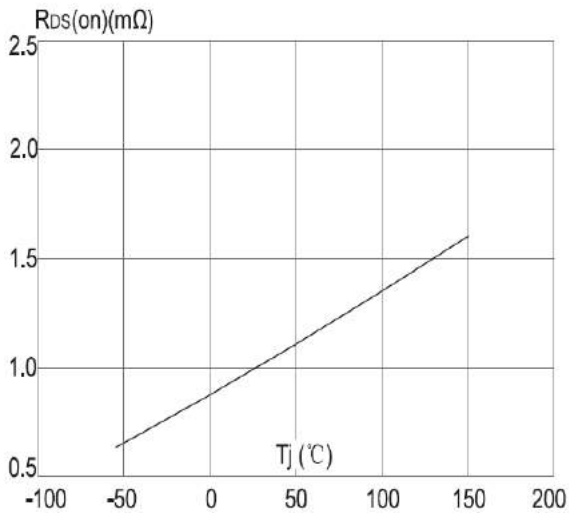


Figure 8: Normalized on Resistance vs. Junction Temperature

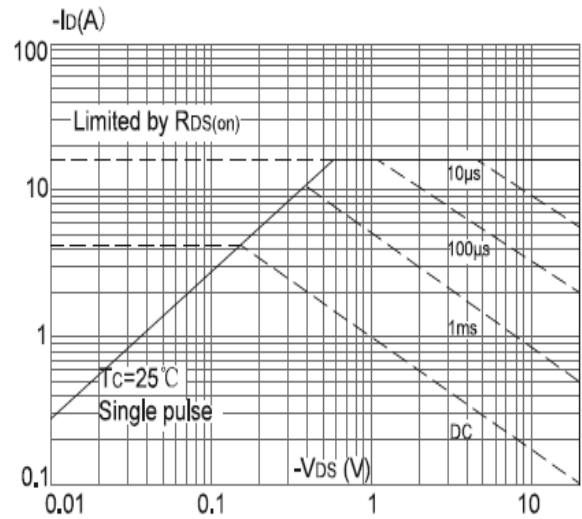


Fig.10 Safe Operating Area

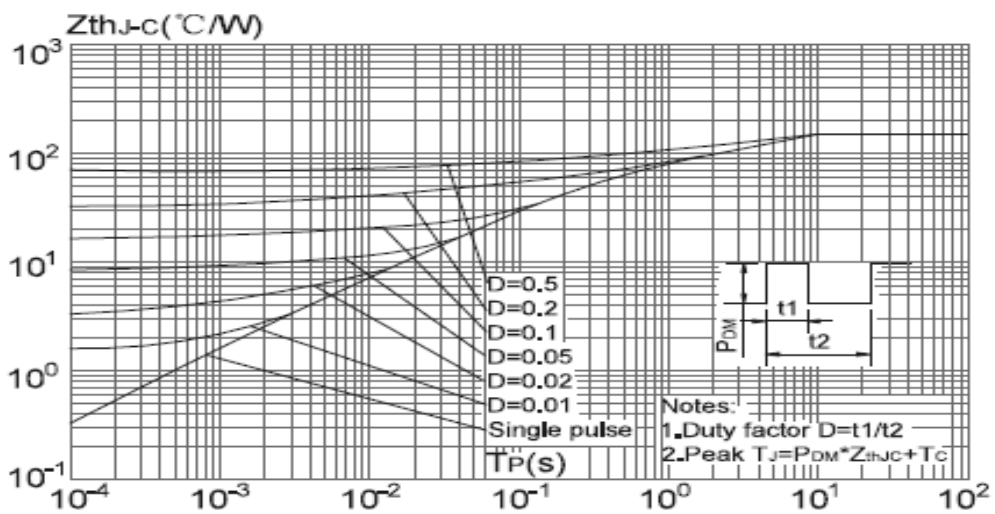
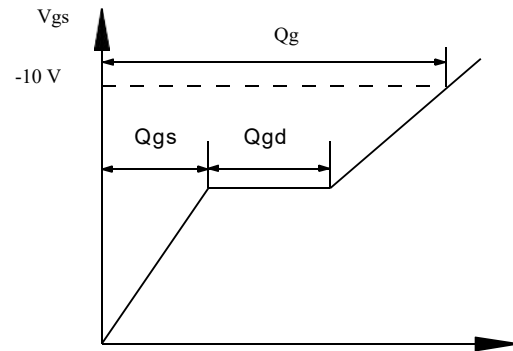
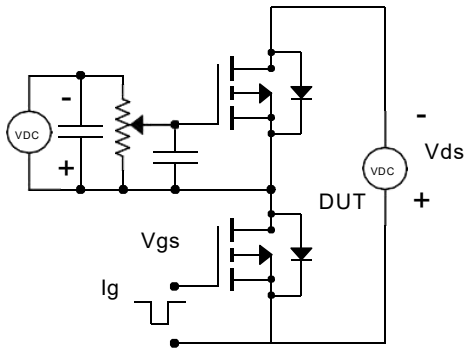
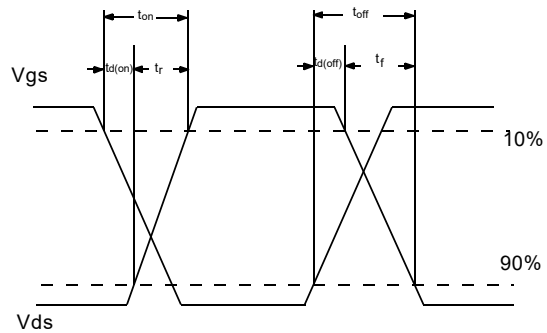
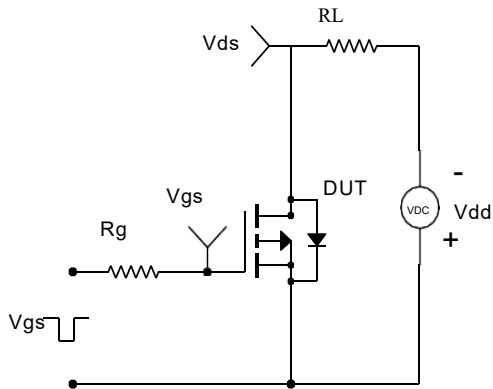


Fig. 11 Transient Thermal Response Curve

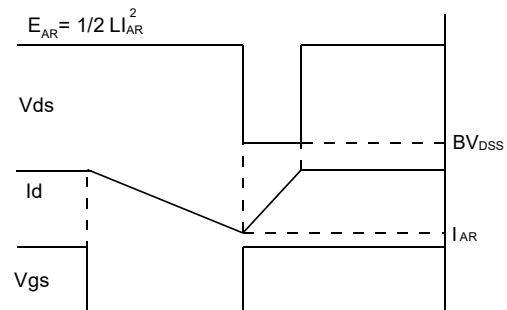
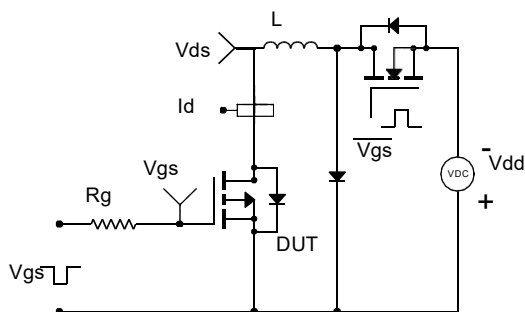
Gate Charge Test Circuit & Waveform



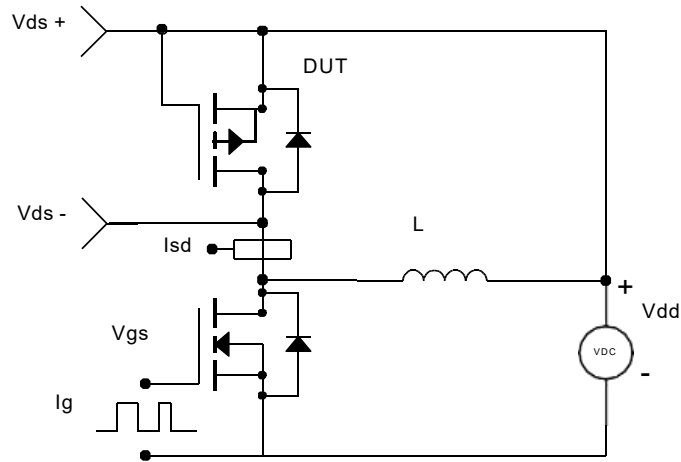
Resistive Switching Test Circuit & Waveforms



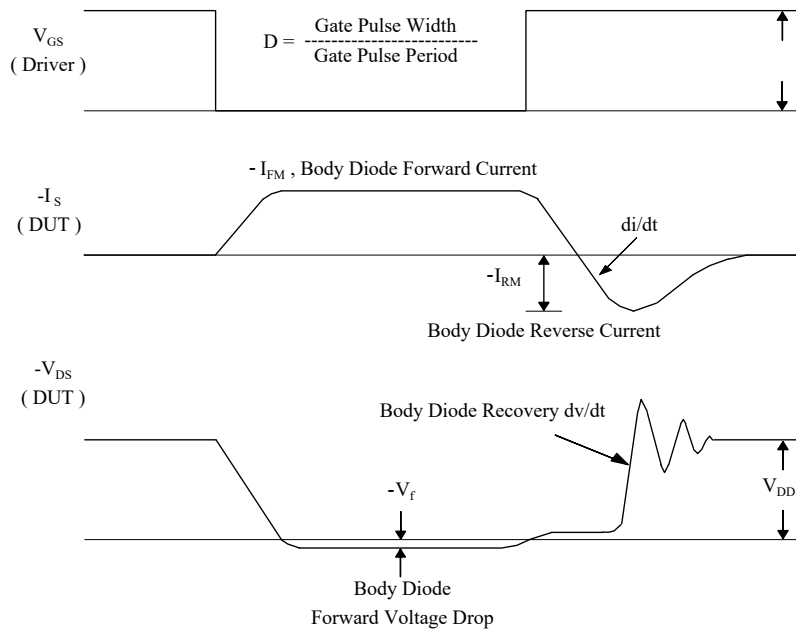
Unclamped Inductive Switching Test Circuit & Waveforms



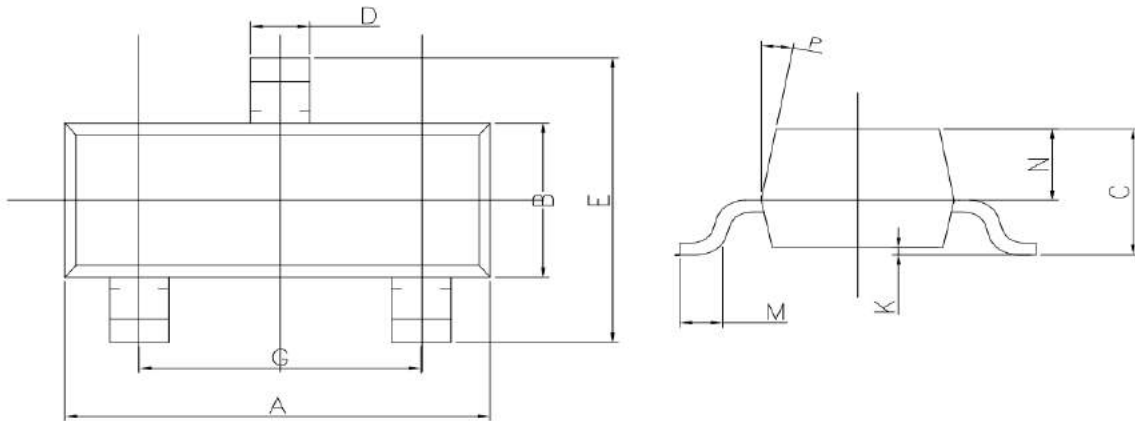
Peak Diode Recovery dv/dt Test Circuit & Waveforms



- dv/dt controlled by R_G
- I_{SD} controlled by pulse period



SOT-23 Package Information



DIM	MILLIMETERS
A	2.90 ± 0.1
B	1.30 ± 0.10
C	0.90 ~ 1.15
D	0.40 ± 0.1
E	2.40 ± 0.15
G	1.90 ± 0.10
K	0.00~0.10
M	0.30MIN
N	0.60 ± 0.10
P	10°TYP

Customer Service

Sales and Service:

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